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# Optoelectronic Integrated Circuit Design and Device Modeling

光电集成电路设计与器件建模

(英文版)

Jianjun Gao



高等教育出版社  
HIGHER EDUCATION PRESS

Studies in Information Science and Technology  
现代信息科学与技术

华东师范大学研究生重点教材建设基金资助

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This edition first published 2011

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Beijing, 100120, P. R. China. All rights reserved.

### 图书在版编目 (CIP) 数据

光电集成电路设计与器件建模 = Optoelectronic Integrated Circuit  
Design and Device Modeling : 英文 / 高建军著. —北京:高等教育  
出版社, 2011. 1

ISBN 978 - 7 - 04 - 031326 - 0

I. ①光… II. ①高… III. ①光集成电路 - 电路设计 - 英文②光  
电器件 - 系统建模 - 英文 IV. ①TN491.02 ②TN15

中国版本图书馆 CIP 数据核字 (2010) 第 257198 号

策划编辑 刘 英      责任编辑 刘 英      封面设计 张 楠  
责任印制 韩 刚

出版发行 高等教育出版社  
社 址 北京市西城区德外大街 4 号  
邮政编码 100120

经 销 蓝色畅想图书发行有限公司  
印 刷 高等教育出版社印刷厂

购书热线 010 - 58581118  
咨询电话 400 - 810 - 0598  
网 址 <http://www.hep.edu.cn>  
<http://www.hep.com.cn>  
网上订购 <http://www.landraco.com>  
<http://www.landraco.com.cn>  
畅想教育 <http://www.widedu.com>

开 本 787 × 1092 1/16  
印 张 19.25  
字 数 350 000

版 次 2011 年 1 月第 1 版  
印 次 2011 年 1 月第 1 次印刷  
定 价 59.00 元

本书如有缺页、倒页、脱页等质量问题,请到所购图书销售部门联系调换。

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物料号 31326 - 00

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# Preface

This textbook is written for the beginning user of optoelectronic integrated circuit (OEIC) design. My purpose is as follows:

- To introduce the basic concepts of optoelectronic devices
- To describe the modeling technique for optoelectronic devices and electronic devices used in high-speed optical systems
- To provide advanced optical transmitter and receiver front-end circuit design techniques.

As we know, state-of-the-art computer-aided design (CAD) methods for OEICs rely heavily on models of real devices. When CAD tools are properly utilized, it is often possible to produce successful designs after only one design iteration. Given the considerable time and cost associated with unnecessary design revisions, CAD tools have proven themselves invaluable to electronic designers. Our primary objective with the present book is to bridge the gap between semiconductor device modeling and IC design by using CAD tools.

Appropriate for electrical engineering and computer science, this book starts with an introduction of an optical fiber communication system, and then covers various lasers, photodiodes, and electronic devices modeling techniques, and high-speed optical transmitter and receiver design. Even for those without a good microwave background, the reader can understand the contents of the book. The presentation of this book assumes only a basic course in electronic circuits as a prerequisite.

The book is intended to serve as a reference book for practicing engineers and technicians working in the areas of radio-frequency (RF), microwave, solid-state devices, and optoelectronic integrated circuit design. The book should also be useful as a textbook for optical communication courses designed for senior undergraduate and first-year graduate students. Especially in student design projects, we foresee that this book will be a valuable handbook as well as a reference, both on basic modeling issues and on specific optoelectronic device models encountered in circuit simulators. The

reference list at the end of each chapter is more elaborate than is common for a typical textbook. The listing of recent research papers should be useful for researchers using this book as a reference. At the same time, students can benefit from it if they are assigned problems requiring reading of the original research papers.

# About the Author



**Jianjun Gao** (M'05–SM'06) was born in Hebei Province, P.R. China, in 1968. He received BEng and PhD degrees from Tsinghua University, in 1991 and 1999, respectively, and an MEng degree from the Hebei Semiconductor Research Institute, in 1994.

From 1999 to 2001, he was a Post-Doctoral Research Fellow at the Microelectronics R&D Center, Chinese Academy of Sciences, developing a PHEMT optical modulator driver. In 2001, he joined the School of Electrical and Electronic Engineering, Nanyang Technological University (NTU), Singapore, as a Research Fellow in semiconductor device modeling and wafer measurement. In 2003, he joined the Institute for High-Frequency and Semiconductor System Technologies, Berlin University of Technology, Germany, as a Research Associate working on the InP HBT modeling and circuit design for high-speed optical communication. In 2004, he joined the Electronics Engineering Department, Carleton University, Canada, as Post-Doctoral Fellow working on semiconductor neural network modeling techniques. From 2004 to 2007, he was a Full Professor with the Radio Engineering Department at Southeast University, Nanjing, China. Since 2007, he has been a Full Professor with the School of Information Science and Technology, East China Normal University, Shanghai, China. He has authored *RF and Microwave Modeling and Measurement Techniques for Field Effect Transistors* (USA SciTech Publishing, 2009). His main areas of research are characterization, modeling, and wafer measurement of microwave semiconductor devices, optoelectronic devices, and high-speed integrated circuit for radio-frequency and optical communication.

Dr Gao is currently a member of the editorial board of *IEEE Transactions on Microwave Theory and Techniques*.

Home page: [http://faculty.ecnu.edu.cn/gaojianjun/info\\_eng.html](http://faculty.ecnu.edu.cn/gaojianjun/info_eng.html).

# Nomenclature

## Units

nm	nanometer, one-billionth of a meter ( $= 10^{-9}$ m)
$\mu$ m	micrometer, one-millionth of a meter ( $= 10^{-6}$ m)
fs	femtosecond, one-millionth of a billionth of a second ( $= 10^{-15}$ s)
ps	picosecond, one-thousandth of a billionth of a second ( $= 10^{-12}$ s)
ns	nanosecond, one-billionth of a second ( $= 10^{-9}$ s)
GHz	gigahertz, 1 billion vibrations per second ( $= 10^9$ Hz)
THz	terahertz, 1000 billion vibrations per second ( $= 10^{12}$ Hz)
mW	milliwatt, one-thousandth of a watt ( $= 10^{-3}$ W)
Mb/s	1 million bits per second ( $= 10^6$ bits per second)
Gb/s	1 billion bits per second ( $= 10^9$ bits per second)
Tb/s	1000 billion bits per second ( $= 10^{12}$ bits per second)
$c$	speed of light in vacuum, 300 million kilometers per second ( $= 3 \times 10^8$ m/s)
$h$	Plank's constant ( $= 6.626 \times 10^{-34}$ J s)
$k$	Boltzmann's constant ( $= 1.38 \times 10^{-23}$ J/K)
fF	femtofarad, one-billionth of a farad ( $= 10^{-15}$ F)
pF	picofarad, one-thousandth of a billionth of a farad ( $= 10^{-12}$ F)
nF	nanofarad, one-billionth of a farad ( $= 10^{-9}$ F)
nH	nanohenry, one-billionth of a henry ( $= 10^{-9}$ H)
pH	picohenry, one-thousandth of a billionth of a henry ( $= 10^{-12}$ H)

## Abbreviations

2-D	two-dimensional
AC	alternating current

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AGC	automatic gain control
AlGaAs	aluminum gallium arsenide
APD	avalanche photodiode
BER	bit error rate/ratio
BFL	buffered FET logic
BH	buried heterostructure
BJT	bipolar junction transistors
CAD	computer-aided design
CPW	coplanar waveguide
CW	continuous wave
DA	distributed amplifier
DBR	distributed Bragg reflector
DC	direct current
DCFL	direct-coupled FET logic
DFB	distributed feedback lasers
DH	double heterojunction
DMUX	demultiplexer
DSM	dynamic-single-mode
DWDM	dense wavelength division multiplexing
EA	electroabsorption
ECL	emitter coupled logic
ER	extinction ratio
FM	frequency modulation
FP	<i>Fabry–Perot</i>
GaAs	gallium arsenide
GMIC	optoelectronic glass microwave integrated circuit
GRIN-SCH	graded index separate confinement heterostructure
HB	harmonic balance
HBT	heterojunction bipolar transistor
HEMT	high electron mobility transistor
HOEIC	hybrid optoelectronic integrated circuits
HZ	high-impedance
IL	insertion loss
IM	intensity modulation
IMD	intermodulation distortion
IM-DD	intensity modulation direct-detection
InP	indium phosphide
I/O	input/output
ITS	intelligent transport system
<i>I–V</i>	current–voltage
laser	light amplification by stimulated emission of radiation
LD	laser diode

LED	light-emitting diode
LiNbO <sub>3</sub>	lithium niobate
MBE	molecular beam epitaxy
MESFET	metal semiconductor field-effect transistor
MMAC	multimedia mobile access communication
MOCVD	molecular organic chemical vapor deposition
MOEIC	monolithic optoelectronic integrated circuit
MOSFET	metal oxide semiconductor field-effect transistor
MQW	multiquantum well
MSM	metal–semiconductor–metal
MUX	multiplexer
M–Z	Mach–Zehnder
NRZ	nonreturn-to-zero
OEIC	optoelectronic devices and integrated circuit
PD	photodiode/photodetector
<i>P–I</i>	power-current
PIC	photonic integrated circuits
QW	quantum-well
RF	radio-frequency
RFIC	radio-frequency integrated circuit
RIN	relative intensity noise
RMS	root mean square
RZ	return-to-zero
SAM	separate-absorption-and-multiplication
SCFL	source-coupled FET logic
SCH	separate confinement heterojunction
SCM	subcarrier multiplexing
SCR	space-charge region
SDFL	Schottky diode FET logic
SI	semi-isolation
SiGe	silicon germanium
SLM	single-longitudinal-mode
SMSR	submode suppression ratio
SNR	signal-to-noise ratio
SPICE	simulation program with integrated circuit emphasis
SQW	single quantum well
TDM	time-division multiplexer
TEN	terminal electrical noise
TIA	transimpedance amplifier
TJS	transverse junction stripe
TZ	transimpedance
UV	ultraviolet

VCSEL	vertical-cavity surface-emitting lasers
VNA	vector network analyzer
VSWR	voltage standing wave ratio
WDM	wavelength division multiplexing

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# 1

## Introduction

The purpose of this chapter is to give an overview of the field of optical communications, and modeling and simulation methods of optoelectronic integrated devices and circuits. The first section of the chapter describes why there are fundamental reasons why optics is attractive for use in communications; the most important components such as the optical transmitter, fiber, and receiver are introduced briefly. In the second section, the conventional computer-aided design (CAD) methods for optoelectronic devices and integrated circuits (ICs) are introduced.

### 1.1 Optical Communication System

The recent explosive growth of data traffic has stimulated the demand for high-capacity information networks. The data need to be transmitted from one place to another at high speed. There are essentially four possible methods to transmit these data [1, 2, 3]:

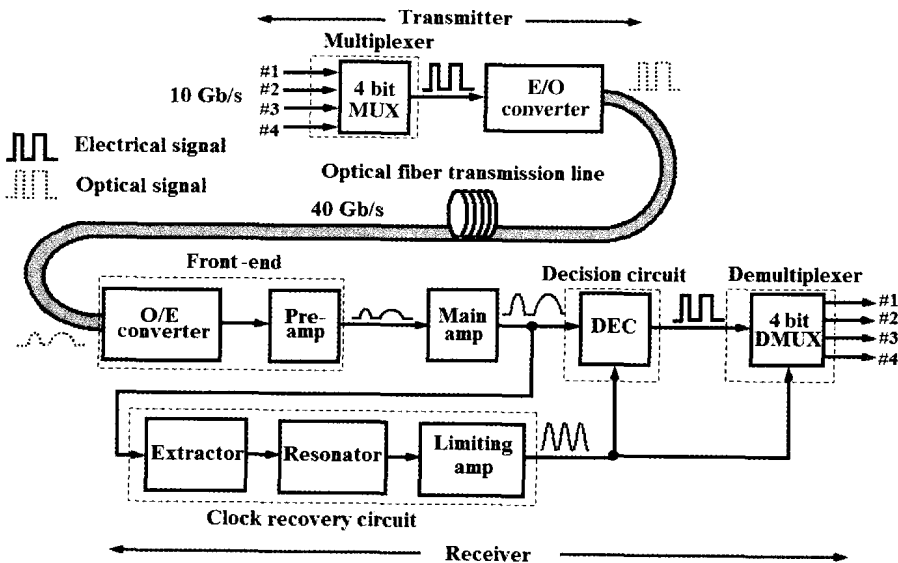
1. Free-space radio-frequency (RF) transmission
2. Free-space optical transmission
3. RF propagation over a fixed transmission line
4. Optical propagation over a fixed fiber-optic transmission line.

Free-space RF transmission is flexible and cheap, but it cannot support large (10 Gb/s) bandwidths and requires fairly large power to transmit over long distances. It is also relatively easy to intercept the transmitted signal, although with sufficient encryption it can be essentially impossible to decode. Free-space optical transmission is also quite flexible, but the signal quality and propagation distance are weather-dependent. Standard RF signal propagation over coaxial cable is simple to integrate with standard electronics and is ideal for relatively short distances and low data rates. Fiber-optic links

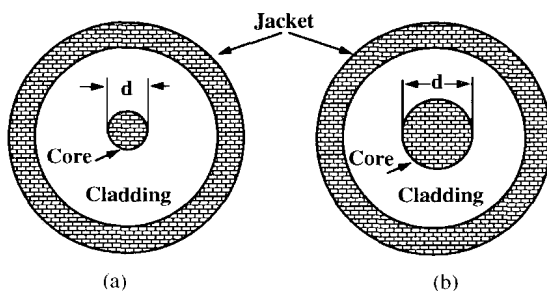
are being used increasingly to replace conventional guided-wave methods of conveying RF signals. Fiber-optical signal distribution is known to possess advantages over conventional signal distribution in cases where the signal must be transmitted over long distances, where signal security or low interference is desired, or where the size, weight, or cost of the distribution hardware is important. Fiber-optical transmission systems can replace normal coaxial or hollow waveguide signal distribution systems if the special characteristics of the electrooptical transducers can be tolerated. An additional advantage that makes millimeter-wave desirable for fiber radio systems is that these frequencies are highly attenuated by water molecules and oxygen in the atmosphere. This can be exploited to limit signal propagation to within the proximity of a picocell, as required for wireless secure communication and for frequency reuse.

Fiber-optic communication is a method of transmitting information from one place to another by sending pulses of light through an optical fiber. The light forms an electromagnetic carrier wave that is modulated to carry information. Optical communication systems have been the mainstream information transmission systems in past decades and are still dominant today thanks to the invention and development of broadband semiconductor lasers, low-loss fibers, fast photodetectors, and other high-quality optoelectronic components. The fiber-optic link has many advantages, which include tremendous available bandwidth ( $\sim 100$  THz), very low transmission loss, immunity to electrical disturbance, and so on; all of this makes a fiber-optic link the preferred transmission solution in many applications.

Figure 1.1 shows a possible scheme for a 40 Gb/s optical transmission system. It requires several high-speed ICs having a bit rate of 40 Gb/s. In the transmitter, a



**Figure 1.1** Schematic diagram of 40 Gb/s optical fiber transmission configuration.



**Figure 1.2** Cross-section of optical fiber: (a) single mode; and (b) multimode.

time-division multiplexer (MUX) combines several parallel data streams (four 10 Gb/s streams in Figure 1.1) into a single data stream with a high bit rate of 40 Gb/s. In the receiver, a demultiplexer (DMUX) splits the 40 Gb/s data stream back into the original four low bit rate streams. The MUX and DMUX are digital medium-scale ICs, which must achieve 40 Gb/s operation with suitably low power dissipation. In the receiver, the extremely small current signal generated by a photodiode is converted into a voltage signal and amplified by a low-noise preamplifier and succeeding main amplifiers having automatic gain control (AGC). The output voltage swing of the amplifier is kept constant, independent of the input signal level. Nevertheless, regeneration, performed by a decision circuit and a clock recovery circuit (composed of a differentiator, rectifier, microwave resonator, and limiting amplifier), is still needed to reduce the timing jitter produced by the cascaded amplifiers. The transmitter and receiver ICs, except for the clock recovery circuit, require broadband operation from near DC to the maximum bit rate with good eye openings.

Compared to the conventional communication system, the difference here is that the communication channel is an optical fiber cable. Figure 1.2 shows the cross-section of single-mode and multimode optical fibres. The cable consists of one or more glass fibers, which act as waveguides for the optical signal (light). In its simplest form an optical fiber consists of a cylindrical core of silica glass surrounded by a cladding whose refractive index is lower than that of the core. Fiber optic cable is similar to electrical cable in its construction, but provides special protection for the optical fiber within. For systems requiring transmission over distances of many kilometers, or where two or more fiber optic cables must be joined together, an optical splice is commonly used.

In multimode fiber, the light is guided by the almost perfect reflection at the interface between the core and cladding. Like multimode optical fibers, single-mode fibers do exhibit modal dispersion resulting from multiple spatial modes, but with narrower modal dispersion. Single-mode fibers are therefore better at retaining the fidelity of each light pulse over long distances than multimode fibers. For these reasons, single-mode fibers can have a higher bandwidth than multimode fibers. Multimode fiber has significantly higher loss (due to modal dispersion) than single-mode fiber and is therefore only used for short distance communications such as within a building or